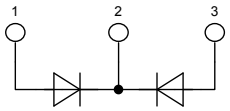
HiPerFRED²

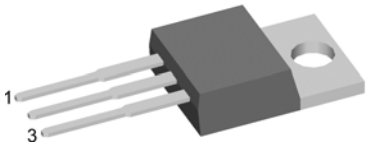
High Performance Fast Recovery Diode
Low Loss and Soft Recovery
Common Cathode

V_{RRM} = 200 V
I_{FAV} = 2x 15 A
t_{rr} = 35 ns

Part number

DPG 30 C 200 PB





Backside: cathode

Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package:

- Housing: TO-220
- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

Ratings

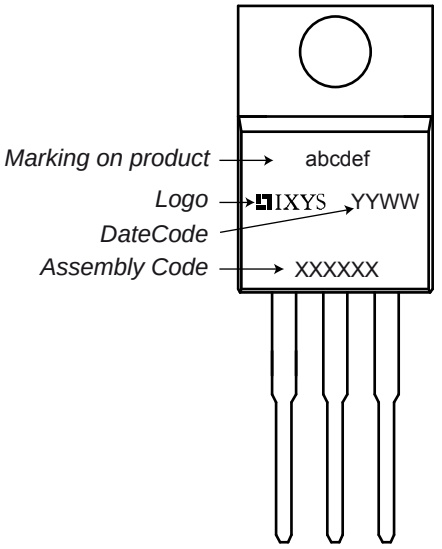
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RRM}	*max. repetitive reverse voltage*		T_{VJ} = 25°C			200	V
I_R	*reverse current*	V_R = 200 V	T_{VJ} = 25°C			1	µA
		V_R = 200 V	T_{VJ} = 150°C			0.08	mA
V_F	*forward voltage*	I_F = 15 A	T_{VJ} = 25°C			1.26	V
		I_F = 30 A				1.51	V
		I_F = 15 A	T_{VJ} = 150°C			1.01	V
		I_F = 30 A				1.29	V
I_{FAV}	*average forward current*	rectangular d = 0.5	T_C = 140°C			15	A
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 175°C			0.69	V
r_F	*slope resistance* }					18	mΩ
R_{thJC}	*thermal resistance junction to case*					1.70	K/W
T_{VJ}	*virtual junction temperature*			-55		175	°C
P_{tot}	*total power dissipation*		T_C = 25°C			90	W
I_{FSM}	*max. forward surge current*	t = 10 ms (50 Hz), sine	T_{VJ} = 45°C			240	A
I_{RM}	*max. reverse recovery current*		T_{VJ} = 25°C		3		A
		I_F = 15 A; V_R = 130 V	T_{VJ} = 125°C		6.5		A
t_{rr}	*reverse recovery time*	$-di_F/dt$ = 200 A/µs	T_{VJ} = 25°C		35		ns
			T_{VJ} = 125°C		55		ns
C_J	*junction capacitance*	V_R = 150 V; f = 1 MHz	T_{VJ} = 25°C		20		pF

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Symbol	Definition	Conditions	Ratings min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per pin [1]			35	A
R_{thCH}	*thermal resistance case to heatsink*			0.50		K/W
T_{stg}	*storage temperature*		-55		150	°C
Weight				2		g
M_D	*mounting torque*		0.4		0.6	Nm
F_C	*mounting force with clip*		20		60	N

[1] I_{RMS} is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip.
In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.

Product Marking



Part number

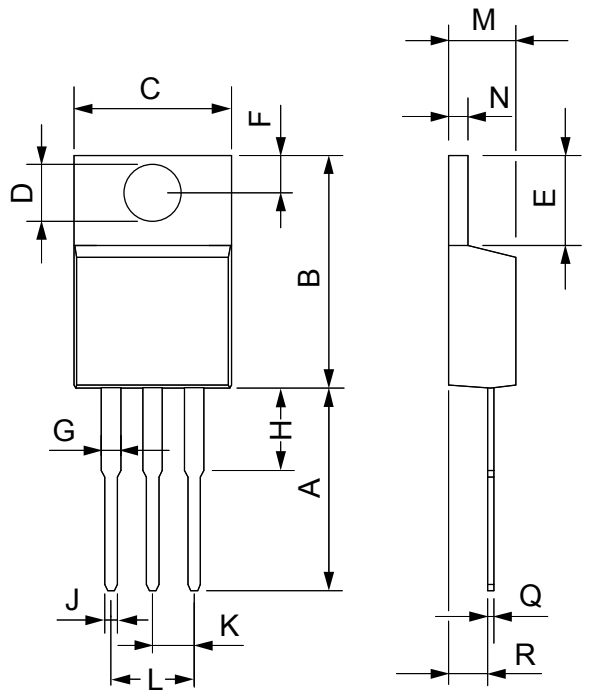
D = Diode
P = HiPerFRED
G = extreme fast
30 = Current Rating [A]
C = Common Cathode
200 = Reverse Voltage [V]
PB = TO-220AB (3)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	DPG 30 C 200 PB	DPG30C200PB	Tube	50	505804

Similar Part	Package	Voltage Class
DPG30C200PC	TO-263AB (D2Pak)	200
DPG30C200HB	TO-247AD (3)	200

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Outlines TO-220



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	12.70	13.97	0.500	0.550
B	14.73	16.00	0.580	0.630
C	9.91	10.66	0.390	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.18	0.100	0.125
G	1.15	1.65	0.045	0.065
H	2.79	5.84	0.110	0.230
J	0.64	1.01	0.025	0.040
K	2.54	BSC	0.100	BSC
M	4.32	4.82	0.170	0.190
N	1.14	1.39	0.045	0.055
Q	0.35	0.56	0.014	0.022
R	2.29	2.79	0.090	0.110

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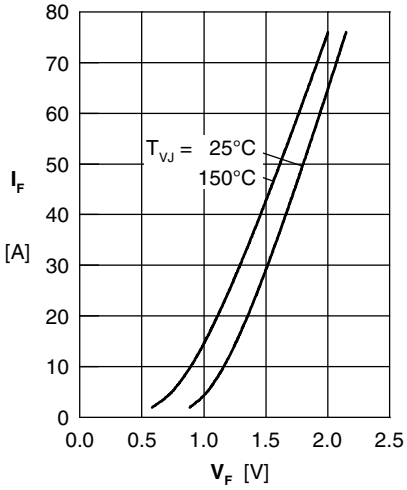


Fig. 1 Forward current I_F vs. V_F

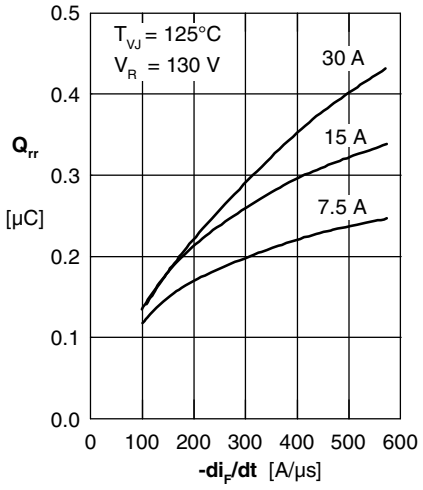


Fig. 2 Typ. reverse recovery charge Q_{rr} versus $-di_F/dt$

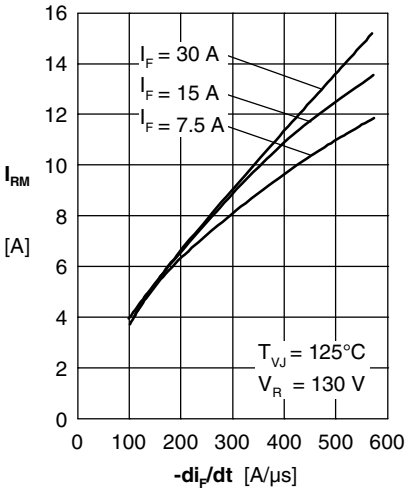


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

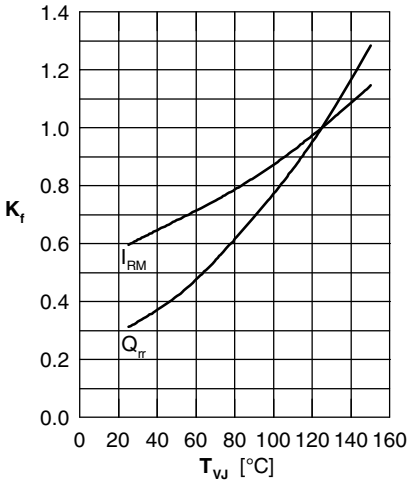


Fig. 4 Dynamic parameters Q_{rr}, I_{RM} versus T_{VJ}

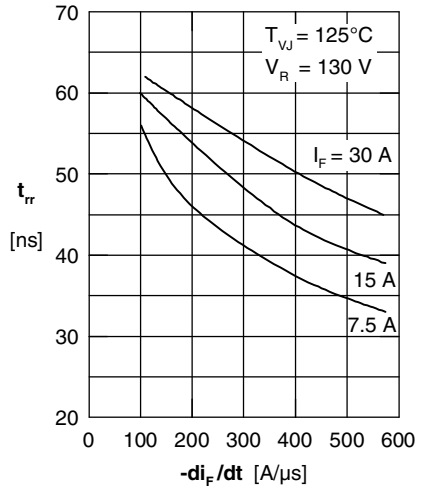


Fig. 5 Typ. recovery time t_{rr} vs. $-di_F/dt$

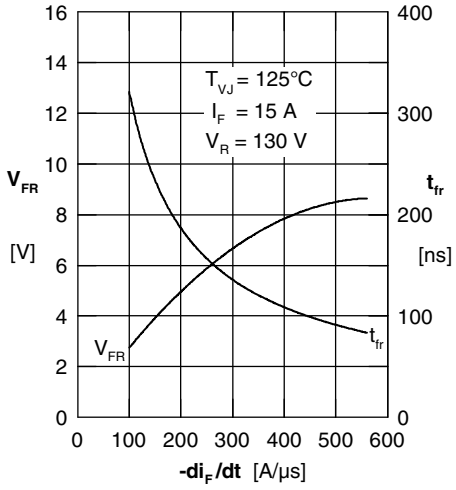


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

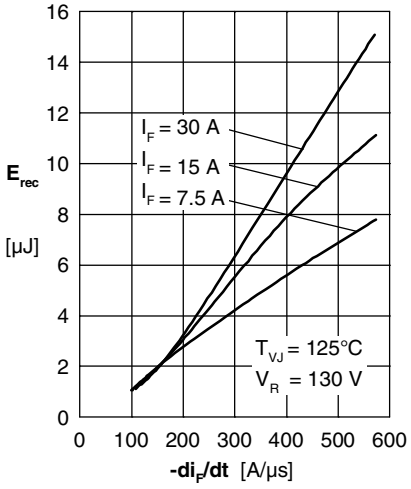


Fig. 7 Typ. recovery energy E_{rec} versus $-di_F/dt$

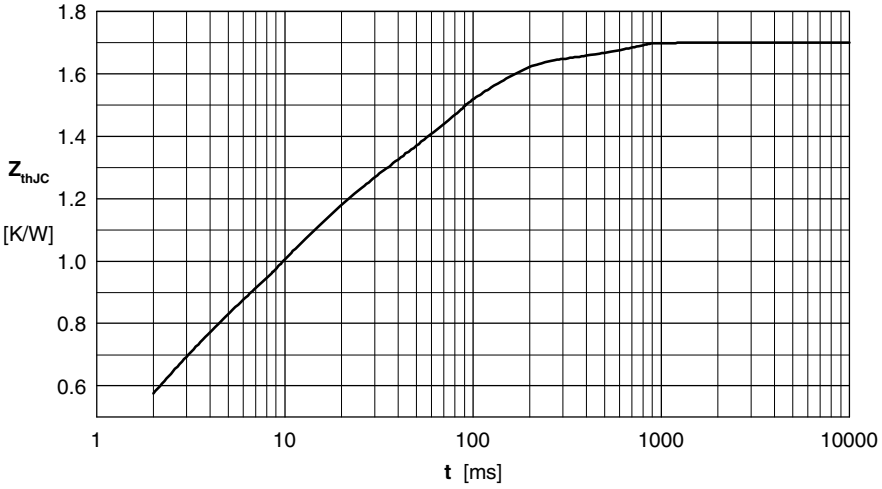


Fig. 8 Transient thermal resistance junction to case

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